

**20V N-CHANNEL ENHANCEMENT MODE MOSFET**

**MAIN CHARACTERISTICS**

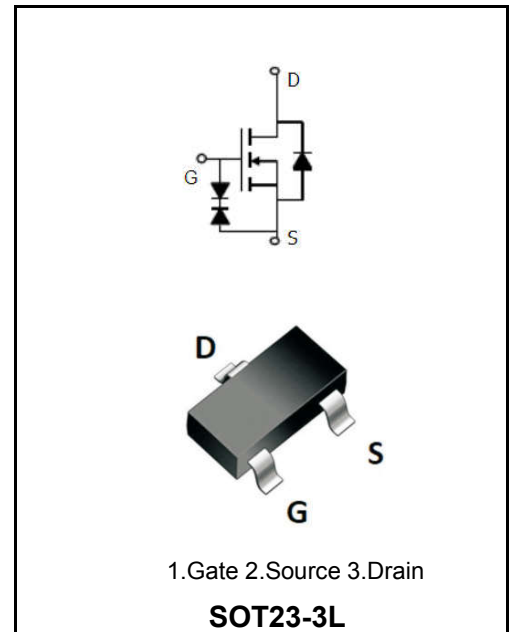
<b>I<sub>D</sub></b>	6.5A
<b>V<sub>DSS</sub></b>	20V
<b>R<sub>DS(on)-typ(@V<sub>GS</sub>=4.5V)</sub></b>	< 33mΩ( <b>Type:21 mΩ</b> )

**Features**

◆ESD=2500HBM

**Application**

- ◆Battery protection
- ◆Load switch
- ◆Uninterruptible power supply



<b>Marking Code</b>	
YFW3416MI	3416

**Maximum Ratings at Tc=25°C unless otherwise specified**

Characteristics	Symbols	Value	Units
Drain-Source Voltage	<b>V<sub>DS</sub></b>	20	<b>V</b>
Gate - Source Voltage	<b>V<sub>GS</sub></b>	±12	<b>V</b>
Drain Current-Continuous	<b>I<sub>D</sub></b>	6.5	<b>A</b>
Drain Current-Pulsed <sup>(Note 1)</sup>	<b>I<sub>DM</sub></b>	30	<b>A</b>
Maximum Power Dissipation	<b>P<sub>D</sub></b>	1.4	<b>W</b>
Operating Junction and Storage Temperature Range	<b>T<sub>J</sub> , T<sub>STG</sub></b>	-55 to +150	<b>°C</b>
Thermal Resistance, Junction-to-Ambient <sup>(Note 2)</sup>	<b>R<sub>θJA</sub></b>	89	<b>°C/W</b>

**Maximum Ratings at Tc=25°C unless otherwise specified**

Characteristics	Test Condition	Symbols	Min	Typ	Max	Units
Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	$BV_{DSS}$	20	-	-	V
Zero Gate Voltage Drain Current	$V_{DS}=20V, V_{GS}=0V$	$I_{DSS}$	-	-	1	$\mu A$
Gate-Body Leakage Current	$V_{GS}=\pm 10V, V_{DS}=0V$	$I_{GSS}$	-	-	$\pm 10$	$\mu A$
Gate -Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	$V_{GS(th)}$	0.45	0.7	1.0	V
Drain-Source On-State Resistance	$V_{GS}=4.5V, I_D=6.5A$	$R_{DS(on)}$	-	17	27	m $\Omega$
	$V_{GS}=2.5V, I_D=5.5A$		-	21	33	
	$V_{GS}=1.8V, I_D=5A$		-	28	40	
Forward Transconductance	$V_{DS}=5V, I_D=6.5A$	$g_{FS}$	8	-	-	S
Input Capacitance	$V_{DS}=10V$ $V_{GS}=0V$ $f=1.0MHz$	$C_{iss}$	-	660	-	$\mu F$
Output Capacitance		$C_{oss}$	-	160	-	
Reverse Transfer Capacitance		$C_{rss}$	-	87	-	
Turn-on delay time	$V_{DD}=10V$ $R_L=1.5\Omega$ $V_{GS}=5V$ $R_{GEN}=3\Omega$	$t_{d(on)}$	-	0.5	-	ns
Turn-on Rise Time		$T_r$	-	1	-	
Turn-Off Delay Time		$t_{d(OFF)}$	-	12	-	
Turn-Off Fall Time		$t_f$	-	4	-	
Total Gate Charge	$V_{DS}=10V$ $I_D=6.5A$ $V_{GS}=4.5V$	$Q_g$	-	8	-	nC
Gate-Source Charge		$Q_{gs}$	-	2.5	-	
Gate-Drain Charge		$Q_{gd}$	-	3	-	
Diode Forward Voltage <sup>(Note 3)</sup>	$V_{GS}=0V, I_S=6.5A$	$V_{SD}$	-	-	1.2	V
Diode Forward Current <sup>(Note 2)</sup>		$I_S$	-	-	6.5	A

**Notes:**

Repetitive Rating: Pulse width limited by maximum junction temperature.

 Surface Mounted on FR4 Board,  $t \leq 10$  sec. Pulse Test:

 Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .

Guaranteed by design, not subject to production

Ratings and Characteristic Curves

Typical Characteristics

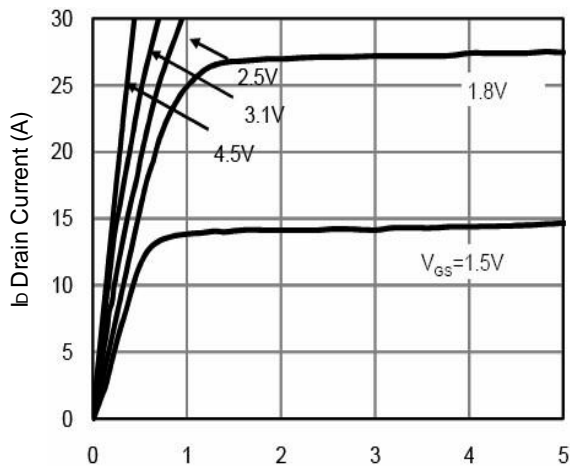


Fig.1 Typical Output Characteristics

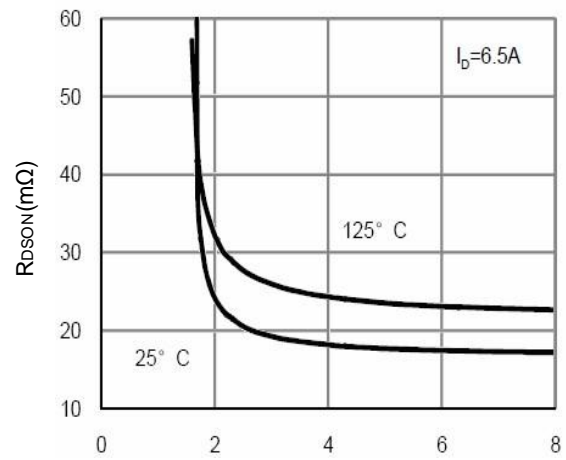


Fig.2 On-Resistance vs. Gate-Source

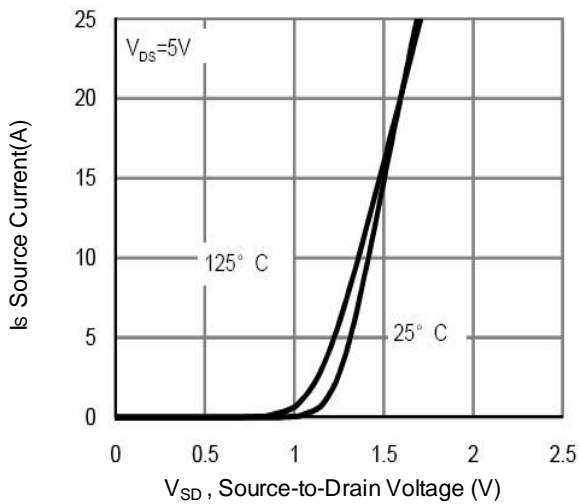


Fig.3 Forward Characteristics of Reverse

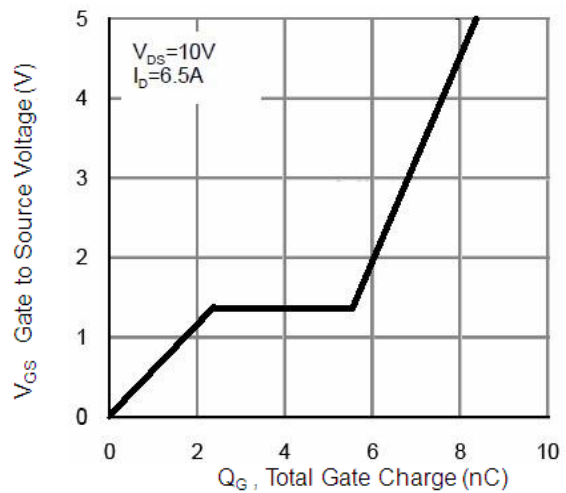


Fig.4 Gate-Charge Characteristics

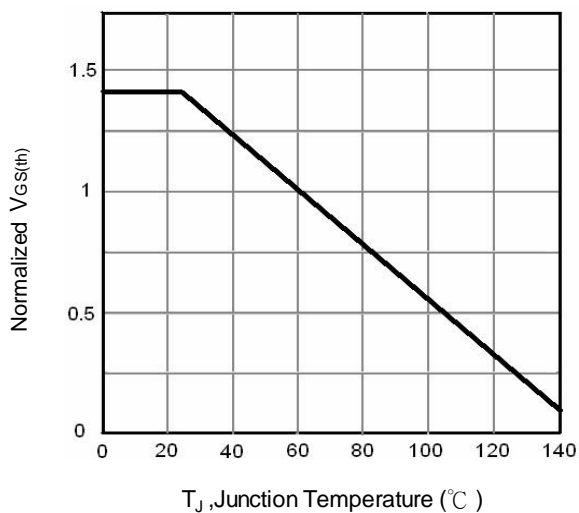


Fig.5 Normalized  $V_{GS(th)}$  vs.  $T_J$

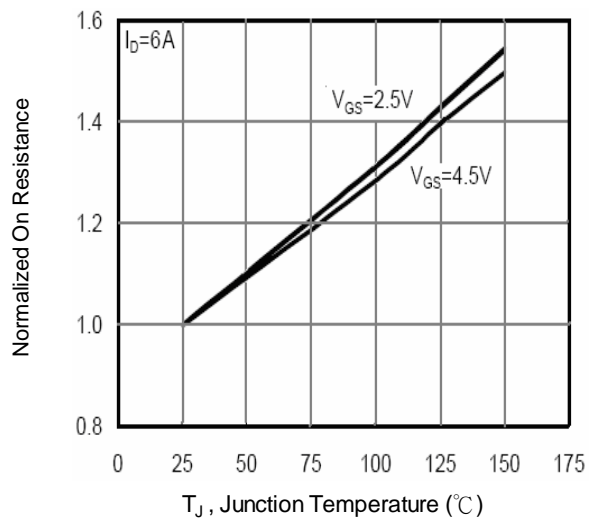


Fig.6 Normalized  $R_{DS(on)}$  vs.  $T_J$

Ratings and Characteristic Curves

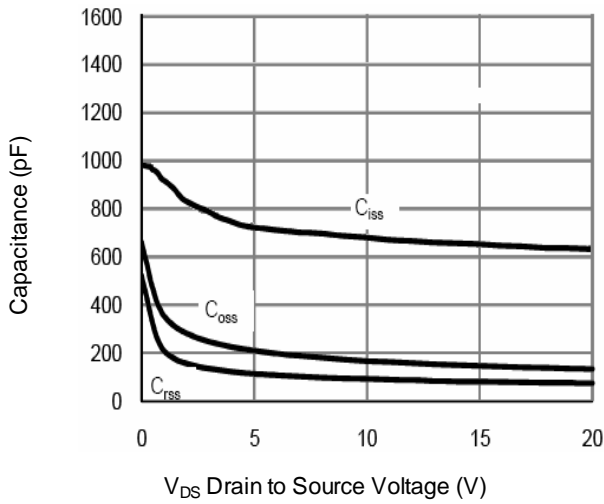


Fig.7 Capacitance

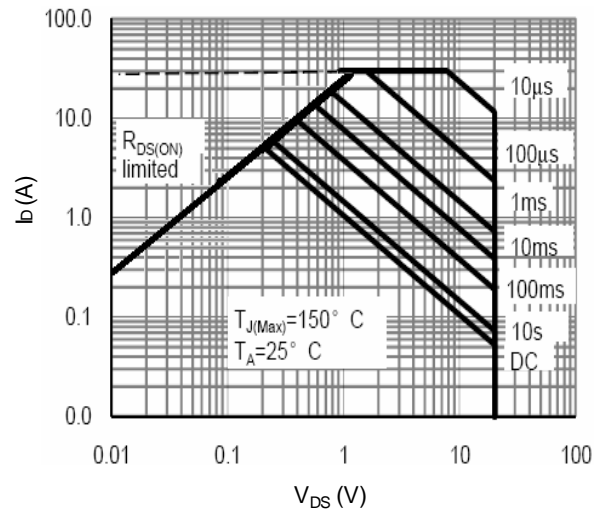


Fig.8 Safe Operating Area

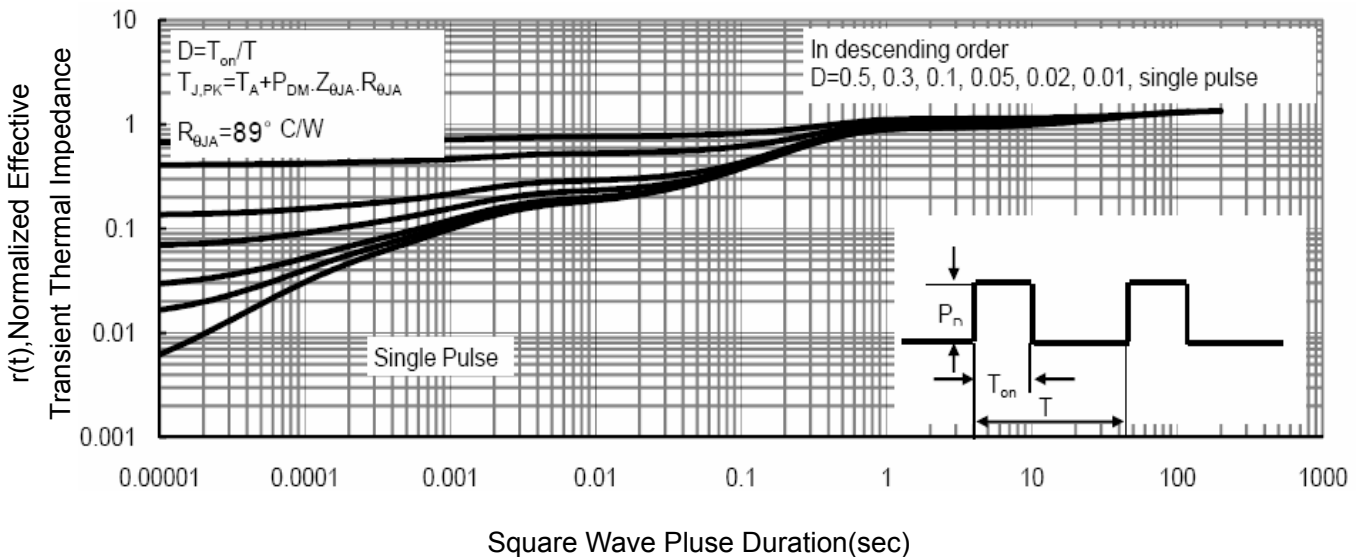


Fig.9 Normalized Maximum Transient Thermal Impedance

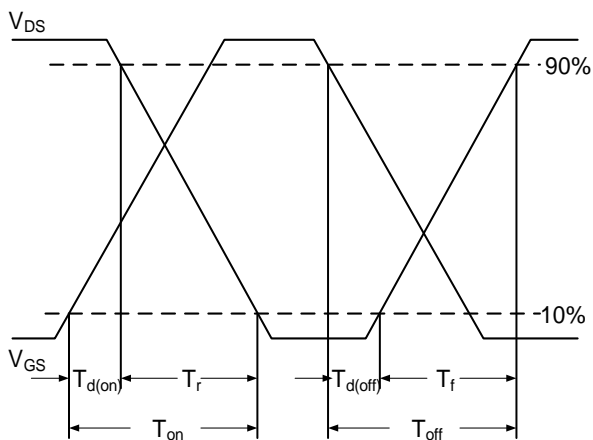


Fig.10 Switching Time Waveform

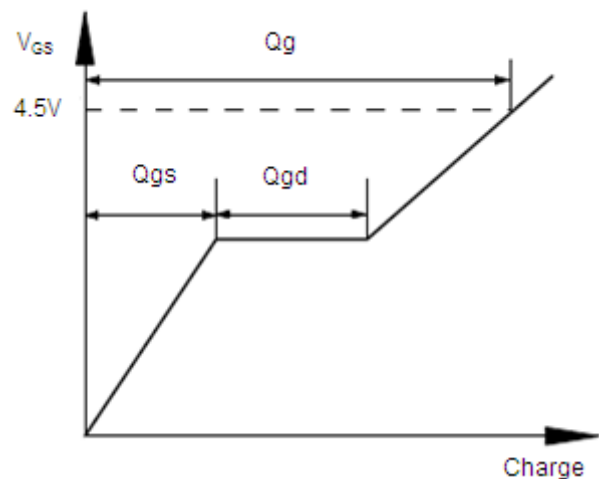


Fig.11 Gate Charge Waveform

**Ordering information**

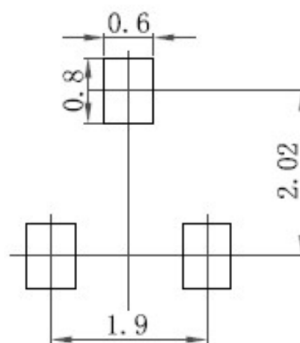
Package	Packing Description	Base Quantity	Packing Quantity
SOT23-3L	Tape/Reel, 7" reel	3000pcs/Reel	24000PCS/Box 120000PCS/Carton

**Package Dimensions**

**SOT23-3L**

Dim.	Millimeter (mm)		mil	
	Min.	Max.	Min.	Max.
A	1.05	1.25	41	49.2
A1	0.10		3.93	
A2	1.05	1.15	41	45
b	0.30	0.50	12	20
c	0.10	0.20	3.93	7.9
D	2.82	3.02	111	119
E	1.50	1.70	59	67
E1	2.65	2.95	104	116
e	0.95		37.4	
e1	1.80	2.00	71	78
L	0.30	0.066	12	26
Θ	8°			

**The recommended mounting pad size**



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